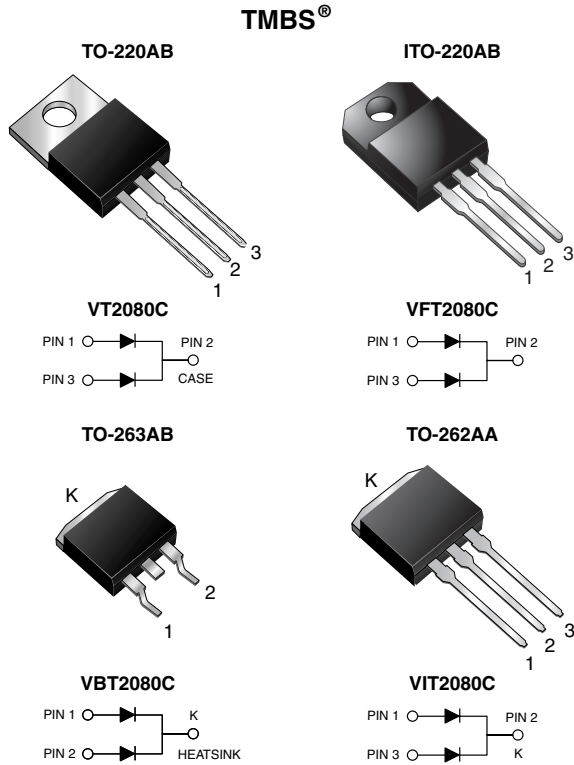


## Dual Trench MOS Barrier Schottky Rectifier

Ultra Low  $V_F = 0.52\text{ V}$  at  $I_F = 5\text{ A}$



### FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB, ITO-220AB, and TO-262AA package)
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

### MECHANICAL DATA

**Case:** TO-220AB, ITO-220AB, TO-263AB and TO-262AA

Molding compound meets UL 94 V-0 flammability rating  
Base P/N-E3 - RoHS compliant, commercial grade

**Terminals:** Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

**Polarity:** As marked

**Mounting Torque:** 10 in-lbs maximum

### PRIMARY CHARACTERISTICS

|                              |          |
|------------------------------|----------|
| $I_{F(AV)}$                  | 2 x 10 A |
| $V_{RRM}$                    | 80 V     |
| $I_{FSM}$                    | 100 A    |
| $V_F$ at $I_F = 10\text{ A}$ | 0.60 V   |
| $T_J$ max.                   | 150 °C   |

### MAXIMUM RATINGS ( $T_A = 25\text{ °C}$ unless otherwise noted)

| PARAMETER   | SYMBOL         | VT2080C       | VFT2080C | VBT2080C | VIT2080C | UNIT |
|---|----------------|---------------|----------|----------|----------|------|
| Maximum repetitive peak reverse voltage   | $V_{RRM}$      | 80            |          |          |          | V    |
| Maximum average forward rectified current (fig. 1)  | per device     | 20            |          |          |          | A    |
|   | per diode      | 10            |          |          |          |      |
| Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode                            | $I_{FSM}$      | 100           |          |          |          | A    |
| Non-repetitive avalanche energy at $T_J = 25\text{ °C}$ , $L = 60\text{ mH}$ per diode                                  | $E_{AS}$       | 110           |          |          |          | mJ   |
| Peak repetitive reverse current at $t_p = 2\text{ }\mu\text{s}$ , 1 kHz, $T_J = 38\text{ °C} \pm 2\text{ °C}$ per diode | $I_{RRM}$      | 1.0           |          |          |          | A    |
| Isolation voltage (ITO-220AB only) from terminal to heatsink $t = 1\text{ min}$   | $V_{AC}$       | 1500          |          |          |          | V    |
| Operating junction and storage temperature range  | $T_J, T_{STG}$ | - 55 to + 150 |          |          |          | °C   |

| ELECTRICAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted) |                         |                         |                    |              |      |      |
|--|-------------------------|-------------------------|--------------------|--------------|------|------|
| PARAMETER  | TEST CONDITIONS         |                         | SYMBOL             | TYP.         | MAX. | UNIT |
| Breakdown voltage  | I <sub>R</sub> = 1.0 mA | T <sub>A</sub> = 25 °C  | V <sub>BR</sub>    | 80 (minimum) | -    | V    |
| Instantaneous forward voltage per diode                                    | I <sub>F</sub> = 5 A    | T <sub>A</sub> = 25 °C  | V <sub>F</sub> (1) | 0.57         | -    | V    |
|  | I <sub>F</sub> = 10 A   |                         |                    | 0.67         | 0.81 |      |
|  | I <sub>F</sub> = 5 A    | T <sub>A</sub> = 125 °C |                    | 0.52         | -    |      |
|  | I <sub>F</sub> = 10 A   |                         |                    | 0.60         | 0.70 |      |
| Reverse current per diode  | V <sub>R</sub> = 80 V   | T <sub>A</sub> = 25 °C  | I <sub>R</sub> (2) | 20           | 600  | μA   |
|  |                         | T <sub>A</sub> = 125 °C |                    | 10           | 20   | mA   |

Notes

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

| THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted) |            |                  |         |          |          |          |      |
|---|------------|------------------|---------|----------|----------|----------|------|
| PARAMETER   |            | SYMBOL           | VT2080C | VFT2080C | VBT2080C | VIT2080C | UNIT |
| Typical thermal resistance  | per diode  | R <sub>θJC</sub> | 3.0     | 6.0      | 3.0      | 3.0      | °C/W |
|   | per device |                  | 2.0     | 5.0      | 2.0      | 2.0      |      |

| ORDERING INFORMATION (Example) |                |                 |              |               |               |
|--------------------------------|----------------|-----------------|--------------|---------------|---------------|
| PACKAGE                        | PREFERRED P/N  | UNIT WEIGHT (g) | PACKAGE CODE | BASE QUANTITY | DELIVERY MODE |
| TO-220AB                       | VT2080C-E3/4W  | 1.88            | 4W           | 50/tube       | Tube          |
| ITO-220AB                      | VFT2080C-E3/4W | 1.73            | 4W           | 50/tube       | Tube          |
| TO-263AB                       | VBT2080C-E3/4W | 1.36            | 4W           | 50/tube       | Tube          |
| TO-263AB                       | VBT2080C-E3/8W | 1.36            | 8W           | 800/reel      | Tape and reel |
| TO-262AA                       | VIT2080C-E3/4W | 1.44            | 4W           | 50/tube       | Tube          |

RATINGS AND CHARACTERISTICS CURVES

(T<sub>A</sub> = 25 °C unless otherwise noted)

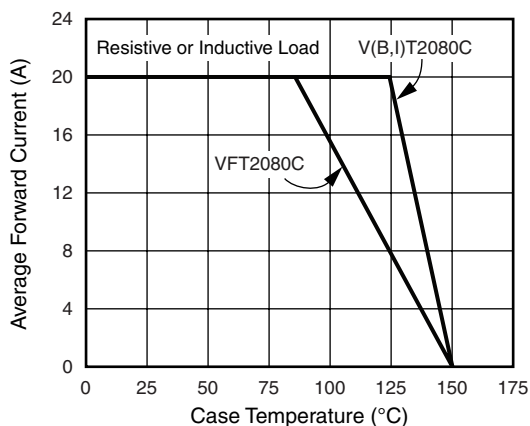


Fig. 1 - Maximum Forward Current Derating Curve

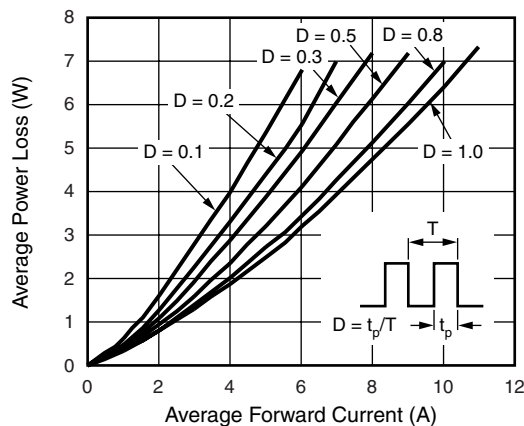


Fig. 2 - Forward Power Loss Characteristics Per Diode

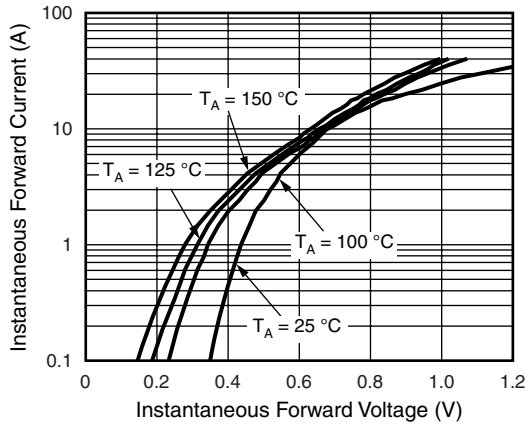


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

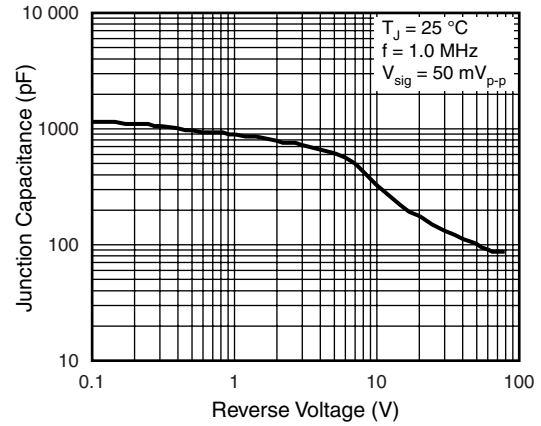


Fig. 5 - Typical Junction Capacitance Per Diode

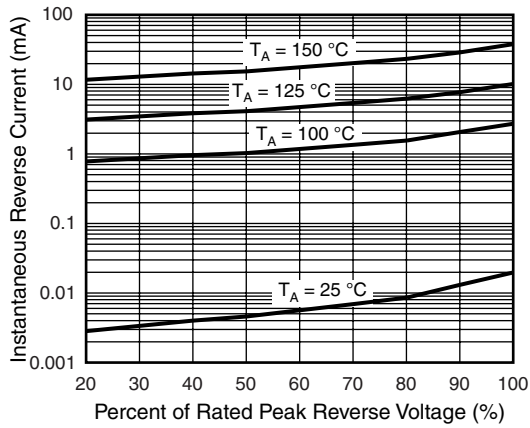


Fig. 4 - Typical Reverse Characteristics Per Diode

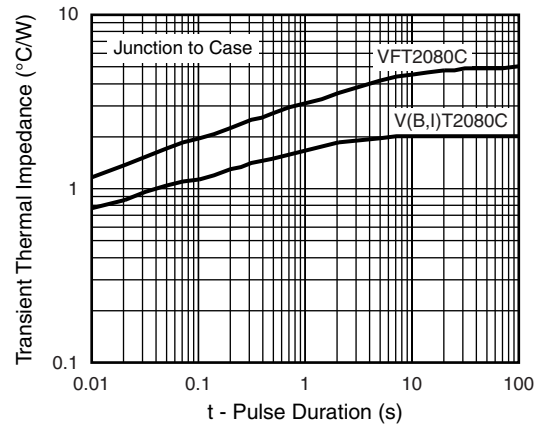


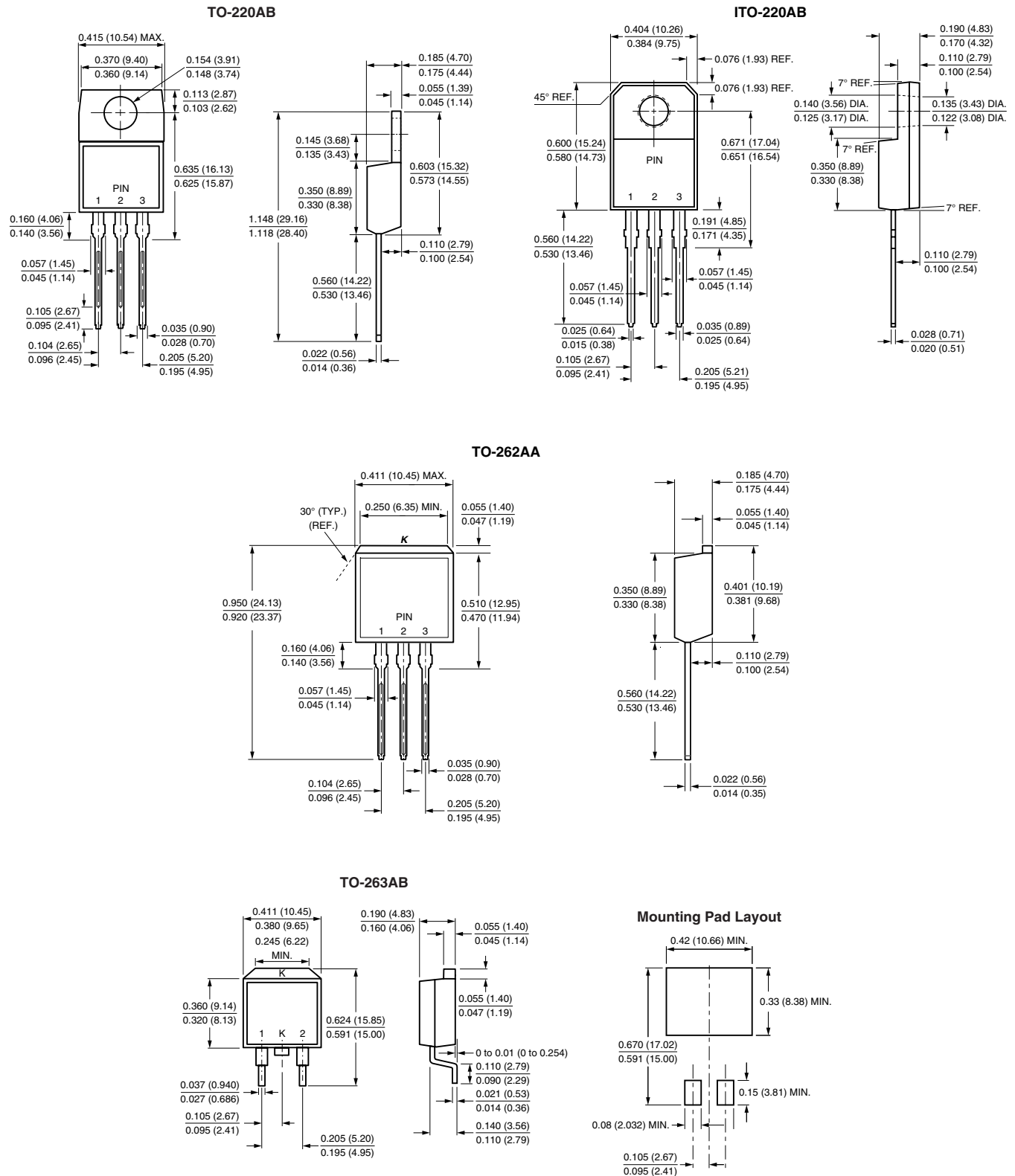
Fig. 6 - Typical Transient Thermal Impedance Per Device

# VT2080C, VFT2080C, VBT2080C, VIT2080C

Vishay General Semiconductor



## PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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